IN THE CLAIMS:

1. (Amended) A dry etching method using a dry etching apparatus having a dual power source capable of independently controlling source power for generating a plasma in a chamber and bias power for drawing ions from the plasma into an object to be etched in the chamber, the method comprising the steps of:

placing a substrate having a member containing at least silicon exposed thereat in the chamber;

introducing a process gas containing at least oxygen into the chamber in which the substrate has been placed; and

performing etching with respect to the member by generating a plasma of the process gas with application of the source power and drawing ions from the plasma into the member with application of the bias power,

the step of performing etching with respect to the member including the step of generating the plasma by initiating the application of the bias power before oxidization proceeds at a surface of the member.

2. (Amended) A dry etching method using a dry etching apparatus having a dual power source capable of independently controlling source power for generating a plasma in a chamber and bias power for drawing ions from the plasma into an object to be etched in the chamber, the method comprising the steps of:

placing a substrate having a member containing at least silicon exposed thereat in the chamber;

introducing a process gas containing at least oxygen into the chamber in which the substrate has been placed; and

performing etching with respect to the member by generating a plasma of the process gas with application of the source power and drawing ions from the plasma into the member with application of the bias power,

wherein the step of performing etching with respect to the member includes the step of initiating the application of the bias power before initiating the application of the source power.

Please add new claims 19 and 20 as follows:

--19. (New) The method of Claim 1, wherein in the step of performing etching with respect to the member, an etching speed of a silicon oxide film is one hundredth or less of an etching speed of silicon.

20. (New) The method of Claim 2, wherein the member is a silicon substrate, a polysilicon film, an amorphous silicon film, or a silicide film.--